AMENDMENTS TO THE CLAIMS

Kindly amend claims **1**, **8**, **9**, **11** and **13**, cancel claim **14**, and add new claims **26-34** as shown in the listing of claims below. This listing of claims will replace all prior versions, and listings of claims in the application.

LISITING OF CLAIMS

Claim 1. (currently amended) A method for a controlled release of structures comprising:

a) forming one or more trenches in a layer of device material;

b) filling one or more selected trenches with an etch-stop material to form one or more etch-stop trenches;

c) defining one or more structures between the selected trenches;

d) forming a structural layer proximate one or more exposed areas of the device layer, wherein the structural layer includes one or more structures that are formed directly on top of an etch-stop layer; and

e) etching one or more portions of the device layer between the etch-stop trenches to release the structures, wherein the etching does not etch the etch-stop material.

Claim 2. (original) The method of claim 1, wherein b) includes depositing etch-stop material over the surface of the device layer.

Claim 3. (original) The method of claim 2 wherein c) includes forming one or more openings in the etch-stop material that has been deposited over the surface of the device layer.

Claim 4. (original) The method of claim 2, wherein the etching undercuts one or more portions of the etch-stop material that has been deposited over the surface of the device layer.

Claim 5. (original) The method of claim 1 where the layer of device material is disposed between two layers of etch-stop material.

Claim 6. (original) The method of claim 1, wherein the device layer includes one or more layers of a silicon-on-insulator (SOI) substrate.

Claim 7. (original) The method of claim 1, wherein the device layer is a layer of glass, quartz or oxide.

Claim 8. (currently amended) The method of claim 1, wherein [[d)]] e includes a wet etch process.

Claim 9. (currently amended) The method of claim 1, wherein [[d)]] e includes a dry etch process.

Claim 10. (cancel)

Claim 11. (currently amended) The method of claim 1, wherein the etch process in [[d)]] e does not etch the structural layer.

Claim 12. (previously presented) The method of claim 1, further comprising releasing one or more portions of the structural layer.

Claim 13. (currently amended) The method of claim 1, wherein the etch process in [[d)]] e releases one or more portions of the structural layer.

Claim 14. (cancel)

Claim 15. (original) The method of claim 14, wherein the structural layer contains two or more sub-layers.

Claim 16. (previously presented) A process for forming structures comprising:

i) forming one or more trenches in a layer of device material;

ii) filling one or more selected trenches with an etch-stop material to form one or more etch-stop trenches;

iii) masking a surface of the layer of device material to expose one or more selected areas of device material that border one or more of the etch-stop trenches; and

iv) forming one or more structures on one or more of the selected areas of the device material that were exposed; and

v) etching one or more of the selected areas of the device layer to release the structures, wherein the etching does not etch the etch-stop material.

Claims 17-22 (cancel)

Claim 23. (previously presented) The method of claim 1, wherein the structural layer is protected by one or more etch-stop layers.

Claim 24. (previously presented) The method of claim 16, wherein one or more of the structures include a device layer protected by one or more etch-stop layers.

Claim 25. (cancel)

Claim 26. (new) The method of claim 16, wherein filling one or more selected trenches with an etch-stop material includes depositing etch-stop material over the surface of the device layer.

Claim 27. (new) The method of claim 26 wherein masking a surface of the layer of device material includes forming one or more openings in the etch-stop material that has been deposited over the surface of the device layer.

Claim 28. (new) The method of claim 26, wherein the etching one or more of the selected areas of the device layer undercuts one or more portions of the etch-stop material that has been deposited over the surface of the device layer.

Claim 29. (new) The method of claim 16 where the layer of device material is disposed between two layers of etch-stop material.

Claim 30. (new) The method of claim 16, wherein the device material includes one or more layers of a silicon-on-insulator (SOI) substrate.

Claim 31. (new) The method of claim 16, wherein the device material includes glass, quartz or oxide.

Claim 32. (new) The method of claim 16, wherein etching one or more of the selected areas of the device layer includes a dry etch or wet etch process.

Claim 33. (new) The method of claim 16, wherein etching one or more of the selected areas of the device layer does not etch the structures.

Claim 34. (new) The method of claim 33, wherein the structures include two or more sub-layers.